Single phase of germanene on Al (111) single crystals: a compelling photoemission study

Borja CAJA-MUNOZ¹
José ÁVILA¹; Céssaire PASQUET¹; Natalia MASSARA²; Michael DERIVAZ²; Didier DEUTEL²; Carmelo PIRRI² and María C. ASENSIO³.

1. Synchrotron SOLEIL, Saint Aubin, BP 48 91192 Gif-sur-Yvette, France
2. Institut de Science des Matériaux de Mulhouse IS2M UMR 7361 CNRS, Université de Haute Alsace, 3 bis rue Alfred Werner, 68057 Mulhouse, France
3. Instituto de Ciencias de Materiales de Madrid (ICMM), CSIC, Cantoblanco, 28049 Madrid, Spain
borjacaja@gmail.com

Germanene, with Ge atoms packed in a honeycomb lattice, like graphene and silicene, is expected to be a promising material with significant theoretical and practical repercussions. Simulations show that Ge monoatomic sheets have as graphene semi-metallic electronic structure character by a linear dispersion around the Dirac point and charge carriers behaving like massless Dirac fermions. Moreover, its large spin–orbit gap, can make experimentally accessible germanene-derived materials with exotic electronic quantum materials. Moreover, the obvious compatibility of germanene with a mature silicon-based nanotechnology makes this material particularly interesting for nano/microelectronics applications. We have grown an atom-thin, ordered, two-dimensional single-phase film in situ through germanium molecular beam epitaxy using an aluminium (111) surface as a substrate. Its growth is similar to the formation of silicene layers on silver (111) templates [1]. The obtained films were characterized by using scanning tunneling microscopy, showing a nearly flat 1H structure, i.e. a network with one Ge atom per unit cell shifted upward with respect to the others [2]. Thanks to a deep high energy resolution synchrotron photoemission study, recording core-level spectroscopy measurements and angle resolved photoemission, (ARPES), we have identified spectroscopic and electronic features characteristics of the (3 × 3) phase of Ge on Al(111) supercell, presenting compelling evidence of the synthesis of the germanene on aluminium [3][4].

References

Figures

Figure 1: Core level Ge 3d line measured on germanene-covered Al(111) taken at a photon energy of 130 eV. This spectrum was recorded at normal photoelectron detection. This spectrum is decomposed into Ge 3d_{5/2} and 3d_{3/2} doublets. Also indicated by the green arrows are the Ge 3d doublets binding energy for bulk Ge (111) crystal.